

KSE350

High Voltage General Purpose Applications

- High Collector-Emitter Breakdown Voltage
- Suitable for Transformer
- Complement to KSE340



PNP Epitaxial Silicon Transistor

Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	- 300	V
V_{CEO}	Collector-Emitter Voltage	- 300	V
V_{EBO}	Emitter-Base Voltage	- 5	V
I_C	Collector Current	- 500	mA
P_C	Collector Dissipation ($T_C=25^\circ\text{C}$)	20	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature	- 65 ~ 150	$^\circ\text{C}$

Electrical Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
BV_{CEO}	Collector-Emitter Breakdown Voltage	$I_C = - 1\text{mA}, I_B = 0$	-300		V
I_{CBO}	Collector Cut-off Current	$V_{CB} = - 300\text{V}, I_E = 0$		-100	μA
I_{EBO}	Emitter Cut-off Current	$V_{BE} = - 3\text{V}, I_C = 0$		-100	μA
h_{FE}	DC Current Gain	$V_{CE} = - 10\text{V}, I_C = - 50\text{mA}$	30	240	

Typical Characteristics

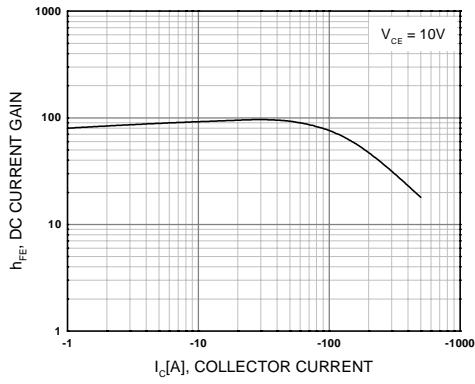


Figure 1. DC current Gain

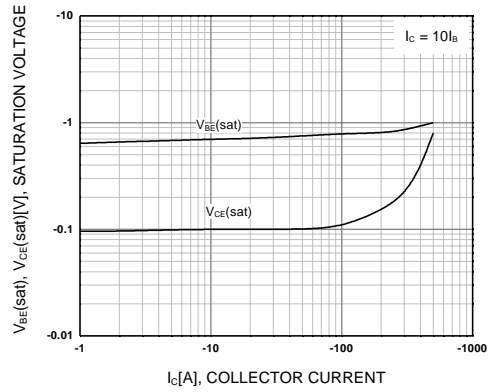


Figure 2. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

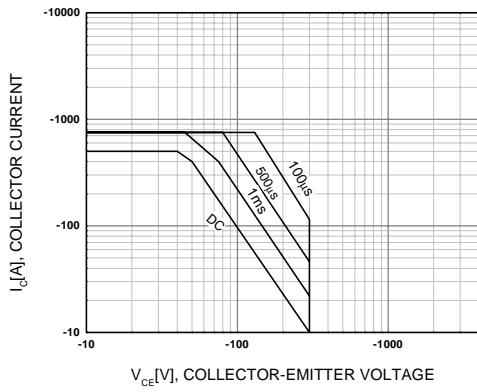


Figure 3. Safe Operating Area

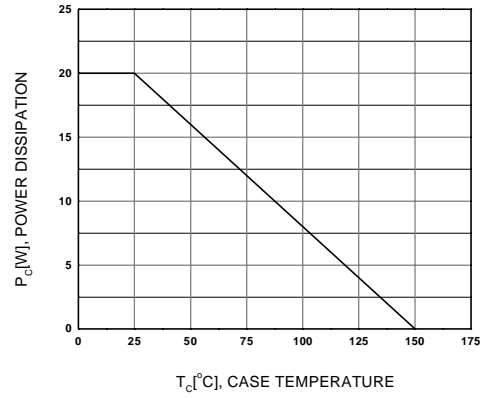


Figure 4. Power Derating

Package Dimensions

TO-126



Dimensions in Millimeters

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Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
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Features

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Applications

High Voltage General Purpose

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Product status/pricing/packaging

Product	Product status	Pricing*	Package type	Leads	Packing method
KSE350S	Full Production	\$0.22	TO-126	3	BULK
KSE350STU	Full Production	\$0.22	TO-126	3	RAIL

* 1,000 piece Budgetary Pricing

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